

# **MSN12203**

## **Preliminary Datasheet**

## N Channel 20V (DS) MOSFET

#### FEATURES

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low Onresistance

PRODUCTY SUMMARY					
V <sub>DS</sub>	R	<sub>DS(on)</sub> <b>m(Ω)</b>	I <sub>D</sub> (A)		
20	12	@V <sub>GS</sub> =4.5V	19.4		
20	15	@V <sub>GS</sub> =2.5V	17.3		

## Application

- Portable Devices
- Consumer Electronics

#### Mechanical

●Case: DFN3333 Package

### **Packing Information**

Package	Packing	
DFN3333	5Kpcs/13"Reel	

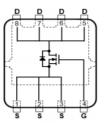
Maximum Ratings (T <sub>A</sub> =25°C unless otherwise specified)				
Parameter	Symbol	Limit	Unit	
DrainSource Voltage	V <sub>DS</sub>	20	V	
GateSource Voltage	V <sub>GS</sub>	±12	V	
Continuous Drain Current <sup>1)</sup>	Ι <sub>D</sub>	20	А	
Maximum Power Dissipation	PD	5	W	
Pulsed Drain Current <sup>2)</sup>	I <sub>DM</sub>	80	А	
Operating Junction and Storage Temperature Range	$T_{J},T_{STG}$	55~150	°C	

Typical Thermal Resistance				
Parameter Symbol Limit				
JunctiontoAmbient Thermal Resistance 3)	$R_{ extsf{ heta}JA}$	65	°C/W	

Note:

- 1. Fused current that based on wire numbers and diameter
- 2. Repetitive Rating: Pulse width limited by the maximum junction temperature
- 3. 1in2 2oz Cu PCB board


**DFN3333** 





Electrical C	haracteristic	CS ( $T_A = 25^{\circ}C$ UNLESS OTH	IERWISE	NOTED)		
Characteristics	Symbol	Toot Condition	Limits			Unit
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit
		Static				
DrainSource Breakdown Voltage	B <sub>VDSS</sub>	$V_{GS} = 0V, I_{D} = 250uA$	20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	0.40	0.63	1.00	V
DrainSource OnState Resistance	P	V <sub>GS</sub> =4.5V, I <sub>D</sub> =19.4A	-	10	12	mΩ
	R <sub>DS(on)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =17.3A	-	12	15	mΩ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	VDS=20V, VGS=0V	-	-	1	uA
GateSource Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±12V, $V_{DS}$ =0V	-	-	±100	nA
		Dynamic <sup>3)</sup>				
Total Gate Charge	$Q_g$		-	16.0	25.60	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =11A, V <sub>GS</sub> =4.5V	-	2.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	4.5	-	nC
Input Capacitance	C <sub>iss</sub>		-	1400	2240	pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	170	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	135	-	pF
	•					
		Switching				
Turn-On Delay Time	t <sub>d(on)</sub>		-	10	-	ns
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =11V, I <sub>D</sub> =1A,	-	13	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =5V,RG=3.3 ଯ	-	28	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	ns
	L		I	I	·	
	Dr	ainSource Diode				
Maximum Continuous Body Diode Forward Current	ا <sub>s</sub>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	-	-	1.2	А
Diode Forward Voltage	V <sub>SD</sub>	IS=1.0A, VGS=0V	-	-	1.5	V

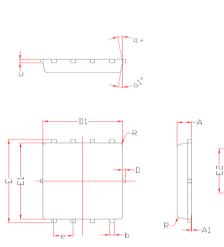
NOTES :

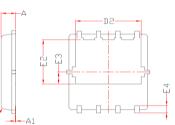
NOTES:
1. Pulse width
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
4. The maximum current rating is package limited.
5. RQJA is the sum of the junctiontocase and casetoambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
6. Guaranteed by design. not subject to production testing.



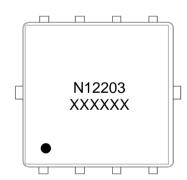
<b>Package Outline Dimensions</b>	(inches and millimeters)
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	Dimensions				
SYMBOL	Millimeters		Inc	hes	
	Min	Max	Min	Max	
А	0.78	0.82	0.031	0.032	
A1	0.00	0.05	0.000	0.002	
b	0.30	0.35	0.012	0.014	
С	0.1	15	0.0	006	
D	0.00	0.05	0.000	0.002	
D1	2.98	3.03	0.117	0.119	
D2	2.35		0.093		
E	3.20	3.25	0.126	0.128	
E1	2.98	3.03	0.117	0.119	
E2	1.75		0.069		
E3	0.58		0.023		
E4	0.350	0.45	0.014	0	
R	0.20		0.008		
е	0.65BSC				
a°	3°				
a1°	10°				





#### **Marking Information**



First line:

AAAAAA = Product number

Second line:

XXXXXX = Tracking number

Third line:Gate Pin Point

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